## NSN 5962-01-168-3366

Memory Microcircuit - Page 1 of 2



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Body Length:         1.290 inches         Body Width:         Between 0.500 inches and 0.610 inches         Body Height:         Between 0.150 inches and 0.210 inches         Maximun Power Dissipation Rating:         950.0 milliwatts         Operating Tempurature Range:         -55.0/+125.0 degrees celsius         Storage Tempurature Range:         -65.0/+150.0 degrees celsius         Peatures Provided:         Hermetically sealed and programmable and wienable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Material:         Ceramic and glass         Inclosure Material:         Output Logic Form:         Transistor-Iransistor logic         Input Grani:         14 input         Case Outline Source And Designator:         19.3 mil-m38510         Positing Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         15. volts power source         Time Rating Per Chateristic:         12.0.0 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         12.000 nanoseconds propagation delay time, low to high level output	
Bedy Width:         Between 0.500 inches and 0.610 inches         Between 0.150 inches and 0.210 inches         Between 0.150 inches and 0.210 inches         Maximun Power Dissipation Rating:         Botto 0.150 inches and 0.210 inches         Maximun Power Dissipation Rating:         Botto 0.150 inches and 0.210 inches         Maximun Power Dissipation Rating:         Botto 0.150 inches and 0.210 inches         Maximun Power Dissipation Rating:         Botto 0.150 inches and 0.210 inches         Botto 0.150 inches and 0.150 inches         Botto 0.150 inches and 0.150 inches         Botto 0.150 inches	Body Length:
Beween 0.500 inches and 0.610 inches           Body Heigh:           Between 0.150 inches and 0.210 inches           Maximum Power Dissipation Rating:           950.0 milliwatts           Operating Tempurature Range:           -55.0/+125.0 degrees celsius           Storage Tempurature Range:           -65.0/+150.0 degrees celsius           Features Provided:           Hermetically sealed and programmable and wienable and 3-state output           Inclosure Material:           Coranic and glass           Inclosure Material:           Dual-in-line           Dual-in-line           Output Logic Form:           Transistor-transistor logic           Intermetically sealed and Designator:           Davalim-line           Output Logic Form:           Transistor-transistor logic           Intermetical Storage Configuration:           Davalim-line           Output Logic Form:           Transistor-transistor logic           Intermetical Storage Configuration:           Davalim-line           Output Logic Form:           Transistor-transistor logic           Intermetical Storage Configuration:           Davalim-line           Store           Cologic Contentexte	
Body Height:         Between 0.150 inches and 0.210 inches         Maximum Power Dissipation Rating:         Body Millwatts         Operating Tempurature Range:         -55.0/125.0 degrees celsius         Storage Tempurature Range:         -65.0/125.0 degrees celsius         Peratures Provided:         Hermetically sealed and programmable and whenable and 3-state output         Hermetically sealed and programmable and whenable and 3-state output         Parlameter Provided:         Caranic and glass         Inclosure Material:         Caranic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Tarsistor-transistor logic         Input Cordic Patterns:         Ostorutin Source And Designator:         Day and-masts10         Yoldage Rating And Type Per Characteristic:         Day for port Source         Yoldage Rating And Type Per Characteristic:         Sto yold sprose source         Time Rating Per Characteristic:         Yoldage Rating And Type per Characteristic:         Sto yold sprose source         Time Rating Per Characteristic:         Rom         Borour Source And Designatorie, low to high level output         M	-
Between 0.150 inches and 0.210 inches         Maximum Power Dissipation Rating:         950.0 milliwatts         Operating Tempurature Range:         -55.0/+125.0 degrees celsius         Storage Tempurature Range:         -65.0/+125.0 degrees celsius         Brading Tempurature Range:         -65.0/+125.0 degrees celsius         Brading Tempurature Range:         -65.0/+150.0 degrees celsius         Brading Tempurature Range:         -65.0/+150.0 degrees celsius         Hermetically sealed and programmable and wienable and 3-state output         Hermetically sealed and programmable and wienable and 3-state output         Iclosure Material:         Caranic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Crucit Pattern:         14 input         Case Outline Source And Designator:         2-3 mil-ma3810         Ternetal Surface Treatment:         5.0 volts power source         7.5 volts power source         Time Rating Per Chacteristie:         2.0 volt nonsoeconds propagation delay time, low to high level output         Momor Pue:         8.0 volt mail         Moutpue:	
Maximu Power Dissipation Rating:         950.0 milliwatts         Operating Tempurature Range:         -55.0/+125.0 degrees celsius         Storage Tempurature Range:         -65.0/+150.0 degrees celsius         Features Provided:         Hermetically sealed and programmable and whenable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Output Logic Form:         Transistor-Itansistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         P-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         Solve power source         Time Rating Per Chacteristic:         12.0.0 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Solder         9.00-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terpinal Type And Quantity:         9.00-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).	Body Height:
950.0 milliwattsOperating Tempurature Range:-55.0/+125.0 degrees celsiusStorage Tempurature Range:-65.0/+150.0 degrees celsiusFetures Provide:Permetically sealed and programmable and whenable and 3-state outputInclosure Material:Coramic and glassInclosure Configuration:Output Logie Form:Transistor logicInput Circuit Pattern:14 inputCase Outline Source And Designator:0-3 mil-m-38510Terminal Surface Treatment:SolderSolder15.0 spores source16.0 spore source17.0 spore source17.0 spore source18.0 spore source19.0	Between 0.150 inches and 0.210 inches
Operating Tempurature Range:         -55.0/+125.0 degrees celsius         Storage Tempurature Range:         -65.0/+150.0 degrees celsius         Features Provided:         Hermetically sealed and programmable and wienable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         D-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Tine Rating Per Chacteristic:         10:0.0 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Source         Test Data Document:         99008-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	Maximum Power Dissipation Rating:
-55.0/12.0 degrees celsius Storage Tempurature Range: -65.0/150.0 degrees celsius Features Provided: Hermetically sealed and programmable and wienable and 3-state output Inclosure Material: Ceramic and glass Inclosure Configuration: Dual-in-line Output Logic Form: Transistor Irgnistor Transistor Irgnistor Inguit Circuit Pattern: 14 input Case Outline Source And Designator: D-3 mil-m-38510 Terminal Surface Treatment: Solder Voltage Rating And Type Per Characteristic: 5.5 volts power source Tine Rating Per Chacteristic: 12.0.00 nanoseconds propagation delay time, low to high level output Memory Device Type: Rom Test Data Document: 99006-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 24 printed circuit	950.0 milliwatts
Storage Tempurature Range:         -65.0/+150.0 degrees celsius         Features Provided:         Hermetically sealed and programmable and w/enable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         0-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         12.0.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Ges00-mil-sel4:83 standard (includes industry or association standards, individual manufactureer standards, etc.)         Terminal Type And Quantity:         24 printed circuit	Operating Tempurature Range:
-65.0/+150.0 degrees celsius         Features Provided:         Hermetically sealed and programmable and w/enable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         0-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         12.0.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Ges00-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)         Terminal Type And Quantity:         24 printed circuit	-55.0/+125.0 degrees celsius
Features Provide:         Hermetically sealed and programmable and w/enable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         D-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         12.0.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Gestional Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)         Terminal Type And Quantity:         24 printed circuit	Storage Tempurature Range:
Hermetically sealed and programmable and w/enable and 3-state output         Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         D-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         120.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Gesto Data Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	-65.0/+150.0 degrees celsius
Inclosure Material:         Ceramic and glass         Inclosure Configuration:         Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         0-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         120.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Test Data Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	Features Provided:
Ceramic and glassInclosure Configuration:Dual-in-lineOutput Logic Form:Transistor-transistor logicInput Circuit Pattern:14 inputCase Outline Source And Designator:D-3 mil-m-38510Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:15. svolts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomCerst Data Document:96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)Cerminal Type And Quantity:24 printed circuit	Hermetically sealed and programmable and w/enable and 3-state output
Inclosure Configuration:Dual-in-lineOutput Logic Form:Transistor-transistor logicInput Circuit Pattern:14 inputCase Outline Source And Designator:D-3 mil-m-38510Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomSolderSolder2.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomSolder-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)Ferminal Type And Quantity:24 printed circuit	Inclosure Material:
Dual-in-line         Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         D-3 mil-m-38510         Terninal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         120.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terninal Type And Quantity:         24 printed circuit	Ceramic and glass
Output Logic Form:         Transistor-transistor logic         Input Circuit Pattern:         14 input         Case Outline Source And Designator:         D-3 mil-m-38510         Terminal Surface Treatment:         Solder         Voltage Rating And Type Per Characteristic:         5.5 volts power source         Time Rating Per Chacteristic:         120.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Fest Data Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	Inclosure Configuration:
Transistor-transistor logicInput Circuit Pattern:14 inputCase Outline Source And Designator:D-3 mil-m-38510Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomFest Data Document:0906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).Ferminal Type And Quantity:24 printed circuit	Dual-in-line
Input Circuit Pattern:14 inputCase Outline Source And Designator:D-3 mil-m-38510Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomSolder	Output Logic Form:
14 input Case Outline Source And Designator: D-3 mil-m-38510 Terminal Surface Treatment: Solder Voltage Rating And Type Per Characteristic: 5.5 volts power source Time Rating Per Chacteristic: 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanosecond	Transistor-transistor logic
Case Outline Source And Designator:D-3 mil-m-38510Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomTest Data Document:96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)Terminal Type And Quantity:24 printed circuit	Input Circuit Pattern:
D-3 mil-m-38510 Terminal Surface Treatment: Solder Voltage Rating And Type Per Characteristic: S.5 volts power source Time Rating Per Chacteristic: 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output Memory Device Type: Rom Forminal Type And Quantity: 24 printed circuit	14 input
Terminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomTest Data Document:96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).Terminal Type And Quantity:24 printed circuit	Case Outline Source And Designator:
Solder Voltage Rating And Type Per Characteristic: 5.5 volts power source Time Rating Per Chacteristic: 120.00 nanoseconds propagation delay time, low to high level output 120.00 nanoseconds propagation delay time, low to high level output Memory Device Type: Rom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 24 printed circuit	D-3 mil-m-38510
Voltage Rating And Type Per Characteristic:5.5 volts power sourceTime Rating Per Chacteristic:120.00 nanoseconds propagation delay time, low to high level outputMemory Device Type:RomTest Data Document:96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).Terminal Type And Quantity:24 printed circuit	Terminal Surface Treatment:
<ul> <li>5.5 volts power source</li> <li>Time Rating Per Chacteristic:</li> <li>120.00 nanoseconds propagation delay time, low to high level output</li> <li>Memory Device Type:</li> <li>Rom</li> <li>Test Data Document:</li> <li>96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).</li> <li>Terminal Type And Quantity:</li> <li>24 printed circuit</li> </ul>	Solder
Time Rating Per Chacteristic:         120.00 nanoseconds propagation delay time, low to high level output         Memory Device Type:         Rom         Test Data Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	Voltage Rating And Type Per Characteristic:
120.00 nanoseconds propagation delay time, low to high level output Memory Device Type: Rom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 24 printed circuit	5.5 volts power source
Memory Device Type: Rom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 24 printed circuit	Time Rating Per Chacteristic:
Rom <b>Test Data Document:</b> 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). <b>Terminal Type And Quantity:</b> 24 printed circuit	120.00 nanoseconds propagation delay time, low to high level output
Test Data Document:         96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).         Terminal Type And Quantity:         24 printed circuit	Memory Device Type:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). <b>Terminal Type And Quantity:</b> 24 printed circuit	Rom
Terminal Type And Quantity:         24 printed circuit	Test Data Document:
24 printed circuit	96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
	Terminal Type And Quantity:
Shelf Life:	24 printed circuit
	Shelf Life:
N/a	N/a
Unit Of Measure:	Unit Of Measure:
	Demilitarization:
	Yes - demil/mli
 Demilitarization:	

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